



STD1805

LOW VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

PRELIMINARY DATA

Ordering Code	Marking	Shipment
STD1805T4	D1805	Tape & Reel
STD1805-1	D1805	Tube

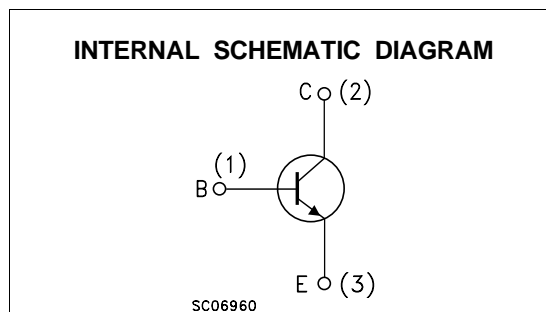
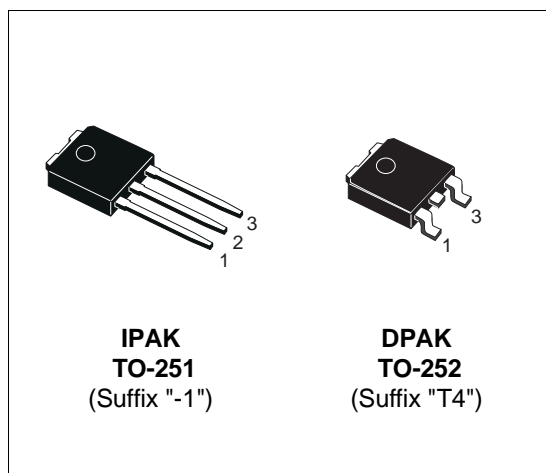
- VERY LOW COLLECTOR TO EMITTER SATURATION VOLTAGE
- HIGH CURRENT GAIN CHARACTERISTIC
- FAST-SWITCHING SPEED
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (Suffix "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (Suffix "T4")

APPLICATIONS:

- CCFL DRIVERS
- VOLTAGE REGULATORS
- RELAY DRIVERS
- HIGH EFFICIENCY LOW VOLTAGE SWITCHING APPLICATIONS

DESCRIPTION

The device is manufactured in NPN Planar Technology by using a "Base Island" layout. The resulting Transistor shows exceptional high gain performance coupled with very low saturation voltage.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage ($I_E = 0$)	150	V
V_{CE0}	Collector-Emitter Voltage ($I_B = 0$)	60	V
V_{EB0}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	5	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	10	A
I_B	Base Current	2	A
P_{tot}	Total Dissipation at $T_c = 25$ °C	15	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

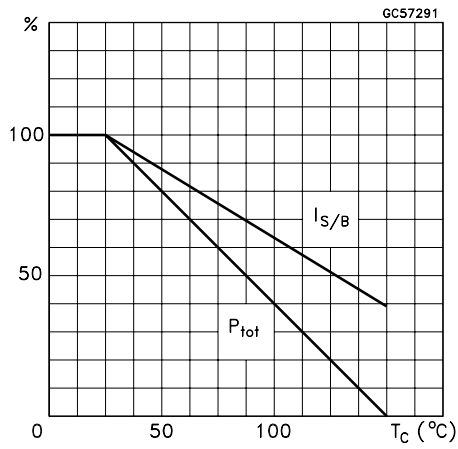
$R_{thj-case}$	Thermal Resistance Junction-case	Max	8.33	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

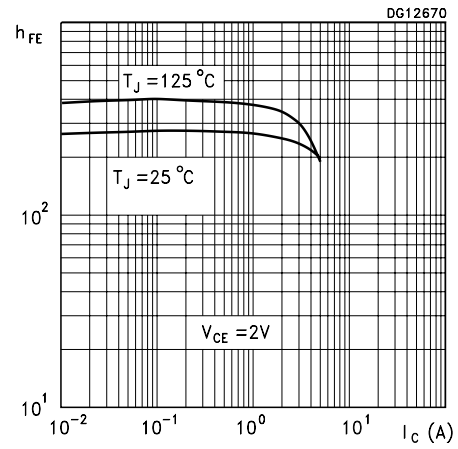
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = 40\text{ V}$				0.1	μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 4\text{ V}$				0.1	μA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = 100\ \mu\text{A}$		150			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = 1\text{ mA}$		60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 100\ \mu\text{A}$		7			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 100\text{ mA}$ $I_C = 2\text{ A}$ $I_C = 3\text{ A}$ $I_C = 5\text{ A}$	$I_B = 5\text{ mA}$ $I_B = 50\text{ mA}$ $I_B = 150\text{ mA}$ $I_B = 200\text{ mA}$		150 200	50 300 400 600	mV mV mV mV
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 2\text{ A}$	$I_B = 100\text{ mA}$		0.9	1.2	V
h_{FE}^*	DC Current Gain	$I_C = 100\text{ mA}$ $I_C = 5\text{ A}$ $I_C = 10\text{ A}$	$V_{CE} = 2\text{ V}$ $V_{CE} = 2\text{ V}$ $V_{CE} = 2\text{ V}$	200 85 20		400	
f_T	Transition frequency	$V_{CE} = 10\text{ V}$	$I_C = 50\text{ mA}$		150		MHz
C_{CBO}	Collector-Base Capacitance	$V_{CB} = 10\text{ V}$	$f = 1\text{ MHz}$		50		pF
t_{ON} t_s t_f	RESISTIVE LOAD Turn- on Time Storage Time Fall Time	$I_C = 1\text{ A}$ $I_{B1} = - I_{B2} = 0.1\text{ A}$	$V_{CC} = 30\text{ V}$		50 1.35 120		ns μs ns

* Pulsed: Pulse duration = 300 μs , duty cycle = 1.5 %

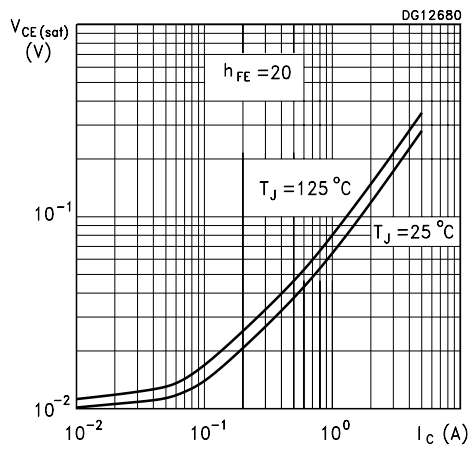
Derating Curve



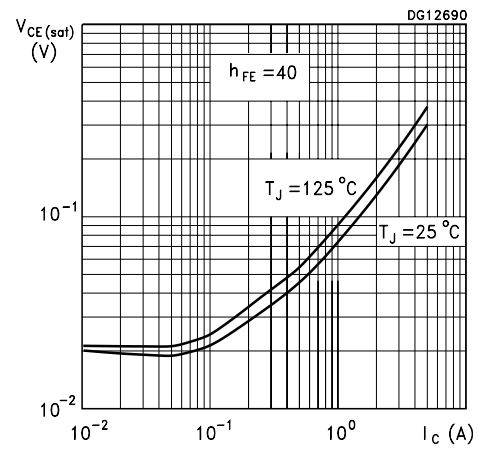
DC Current Gain



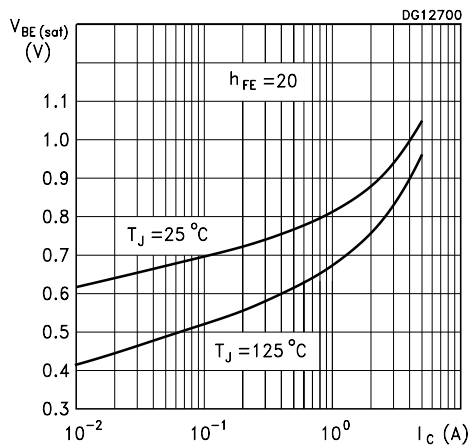
Collector-Emitter Saturation Voltage



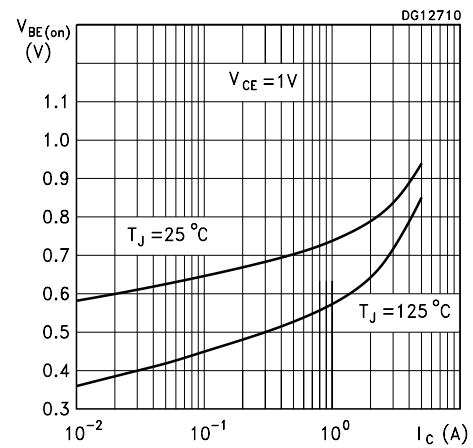
Collector-Emitter Saturation Voltage



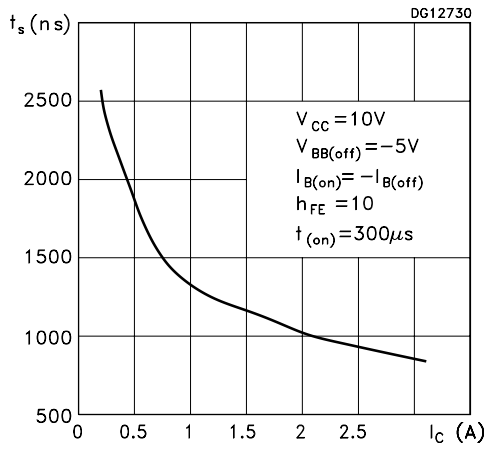
Base-Emitter Saturation Voltage



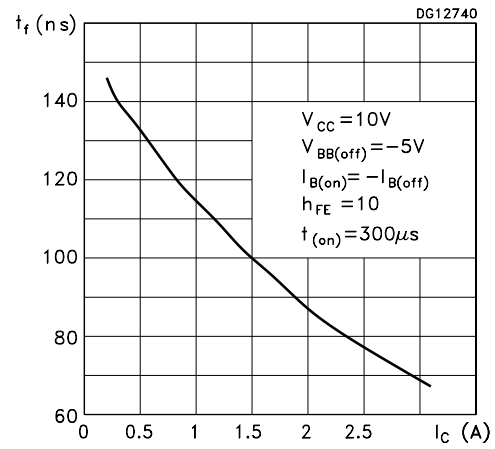
Base-Emitter On Voltage



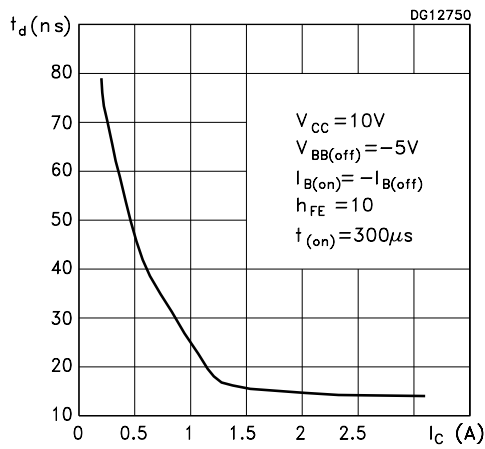
Switching Times Resistive Load



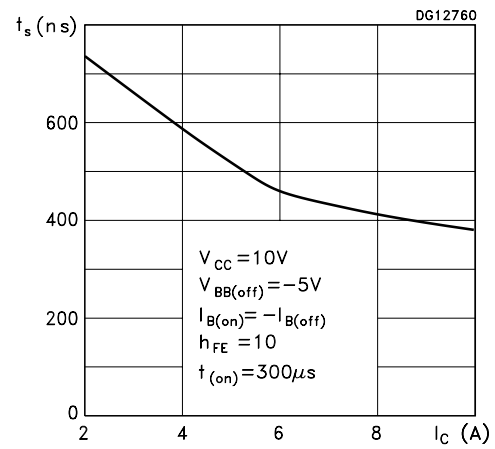
Switching Times Resistive Load



Switching Times Resistive Load



Switching Times Inductive Load



Switching Times Inductive Load

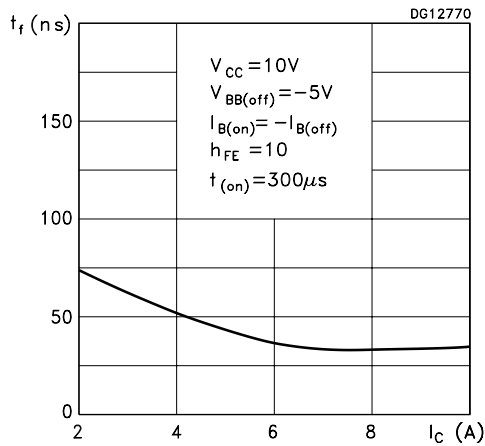
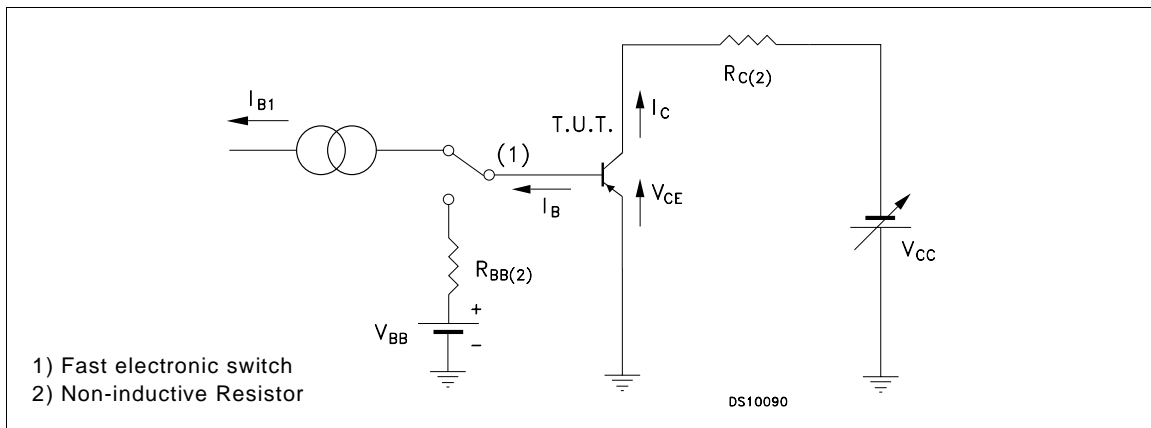
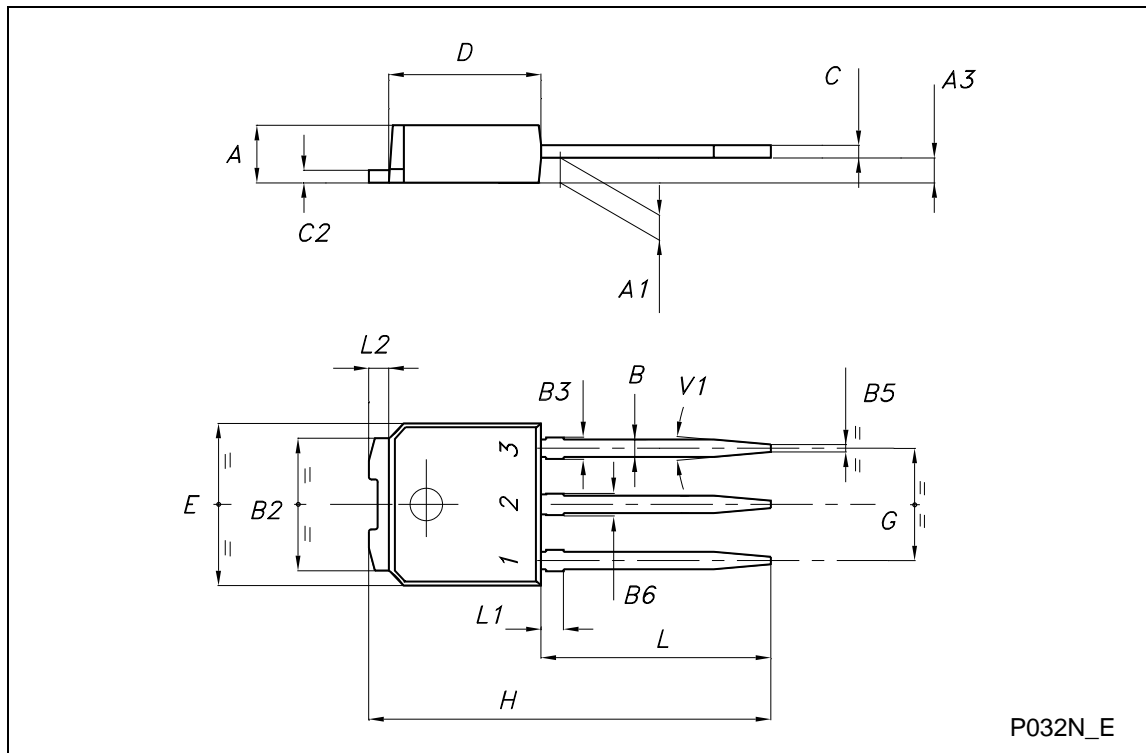


Figure 1: Resistive Load Switching Test Circuit.

TO-251 (IPAK) MECHANICAL DATA

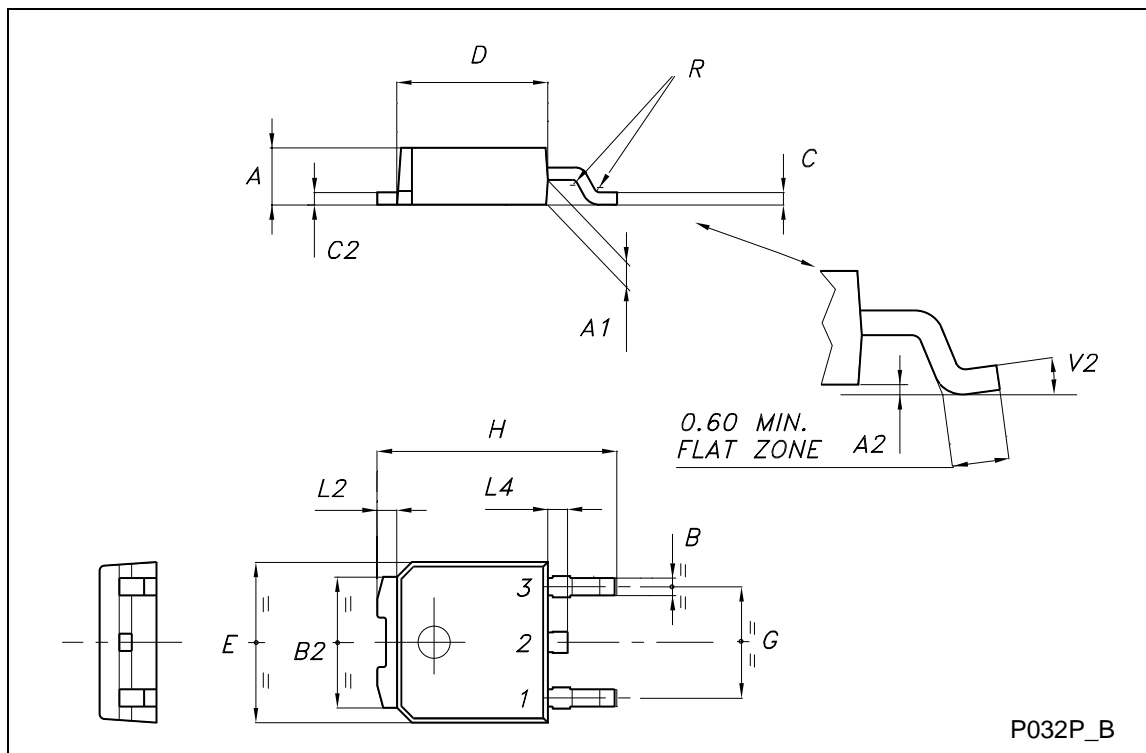
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A3	0.70		1.30	0.028		0.051
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
B3			0.85			0.033
B5		0.30			0.012	
B6			0.95			0.037
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.237		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	15.90		16.30	0.626		0.642
L	9.00		9.40	0.354		0.370
L1	0.80		1.20	0.031		0.047
L2		0.80	1.00		0.031	0.039
V1		10°			10°	



P032N_E

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



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